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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

GODEFRIDUS A.M. HURKX ET AL

PHN 16,741A

Serial No.

Prior Group Art Unit: 2815

Filed: Concurrently

Prior Examiner: M. Warren

SEMICONDUCTOR DEVICE WITH A BIPOLAR TRANSISTOR, AND METHOD OF
MANUFACTURING SUCH A METHOD

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination,
please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claims 1-5 and amend claims 6-10 as follows:

AI Sub C4
6. (Amended) A method of manufacturing a semiconductor device whereby a first semiconductor region is formed in a semiconductor body comprising a substrate, which first semiconductor region lies in the semiconductor body, is of a first conductivity type, forms a collector region of a bipolar transistor, and is provided with a first connection conductor, whereby a second semiconductor region of a second conductivity type opposed to the first is formed above said first semiconductor region, which second semiconductor region forms a base region of the transistor, adjoins the surface of the semiconductor body, and is provided with a second connection conductor at said surface, and whereby a third semiconductor region is formed which is recessed into the second semiconductor